RGWX5TS65

650V 75A Field Stop Trench IGBT

Datasheet

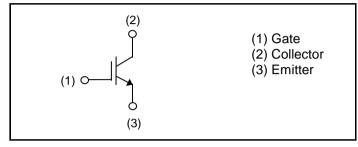
V _{CES}	650V
I _{C (100°C)}	75A
V _{CE(sat) (Typ.)}	1.5V
P_{D}	348W

Outline TO-247N (1) (2)(3)

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

●Inner Circuit



Application

PFC

UPS

Welding

Solar Inverter

ΙH

Packaging Specifications

or ackaging opecinications						
Packaging	Tube					
Reel Size (mm)	-					
Tape Width (mm)	-					
Basic Ordering Unit (pcs)	450					
Packing Code	C11					
Marking	RGWX5TS65					
	Packaging Reel Size (mm) Tape Width (mm) Basic Ordering Unit (pcs) Packing Code					

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

	0	<u> </u>		
Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Callantar Current	T _C = 25°C	I _C	132	Α
Collector Current	T _C = 100°C	I _C	75	Α
Pulsed Collector Current	llsed Collector Current		300	Α
Power Dissipation	T _C = 25°C	P _D	348	W
	T _C = 100°C	P _D	174	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raidilletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.43	°C/W

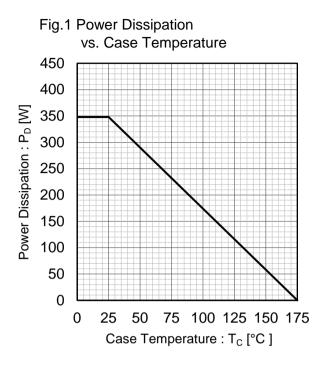
●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

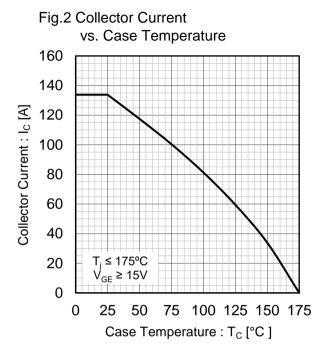
Parameter	Symbol	Conditions		Unit		
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	ı	ı	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	ı	ı	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 50.4 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 75A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.5 1.85	1.9 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			l loit
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	$V_{CE} = 30V$,	-	5980	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	156	-	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	118	-	
Total Gate Charge	Q_g	V _{CE} = 400V,	-	213	-	
Gate - Emitter Charge	Q _{ge}	I _C = 75A,	-	42	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	82	-	
Turn - on Delay Time	t _{d(on)}		-	64	-	
Rise Time	t _r	$I_C = 75A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	31	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	229	-	
Fall Time	t _f	Inductive Load	-	31	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	2.39	-	m l
Turn - off Switching Loss	E _{off}	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	-	1.68	-	+ mJ
Turn - on Delay Time	t _{d(on)}		-	61	-	
Rise Time	t _r	$I_C = 75A, V_{CC} = 400V,$ $V_{GF} = 15V, R_G = 10\Omega,$	-	32	-	
Turn - off Delay Time	t _{d(off)}	T _j = 175°C Inductive Load *E _{on} include diode reverse recovery	-	254	-	ns
Fall Time	t _f		-	51	-	
Turn - on Switching Loss	E _{on}		-	2.32	-	m l
Turn - off Switching Loss	E _{off}		-	1.97	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 300A$, $V_{CC} = 520V$, $V_P = 650V$, $V_{GE} = 15V$, $R_G = 100\Omega$, $T_j = 175^{\circ}C$	FU	LL SQUA	.RE	-

• Electrical Characteristic Curves





1000 1µs 100 10µs Collector Current : I_C [A] 100µs 10 1 0.1 $T_{\rm C} = 25^{\circ}{\rm C}$ Single Pulse 0.01 10 100 1000 Collector To Emitter Voltage: V_{CE} [V]

Fig.3 Forward Bias Safe Operating Area

400 350 Collector Current : Ic [A] 300 250 200 150 100 50 $T_i \le 175^{\circ}C$ V_{GF} = 15V 0 200 400 600 800 Collector To Emitter Voltage: V_{CE} [V]

Fig.4 Reverse Bias Safe Operating Area

• Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

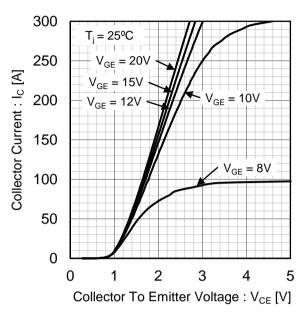


Fig.6 Typical Output Characteristics

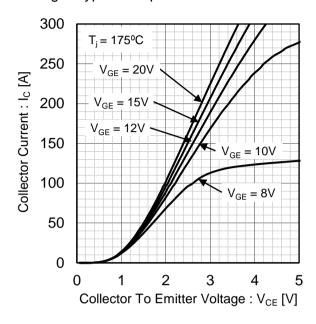


Fig.7 Typical Transfer Characteristics

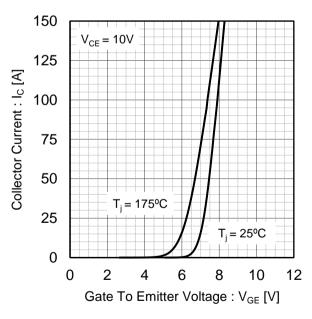
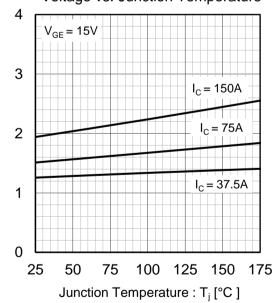


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



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Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

● Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

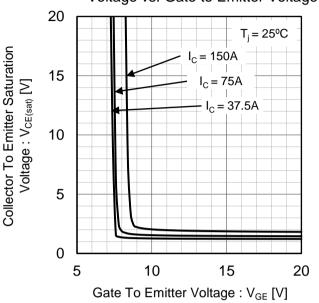


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

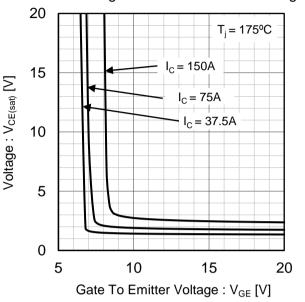


Fig.11 Typical Switching Time vs. Collector Current

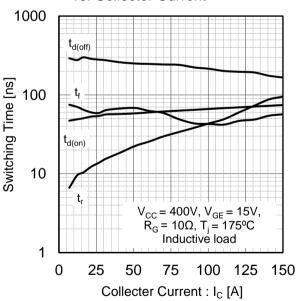
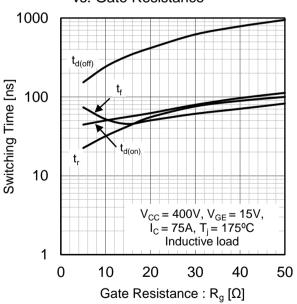


Fig.12 Typical Switching Time vs. Gate Resistance



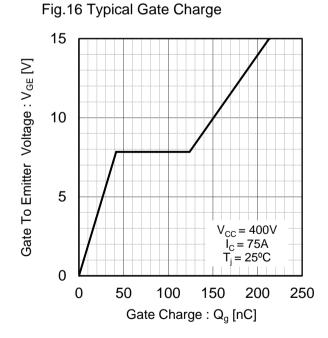
Collector To Emitter Saturation

•Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] Eoff 1 0.1 $V_{CC} = 400V, V_{GE} = 15V,$ $R_G = 10\Omega, T_j = 175^{\circ}C$ Inductive load 0.01 0 25 50 75 100 125 150 Collecter Current : I_C [A]

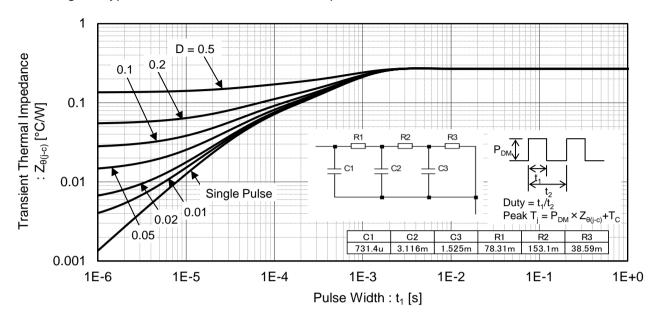
Fig.14 Typocal Switching Energy Losses vs. Gate Resistance 10 Switching Energy Losses [mJ] E_{on} 1 $\mathsf{E}_{\mathsf{off}}$ 0.1
$$\begin{split} &V_{\text{CC}} = 400\text{V}, \, I_{\text{C}} = 75\text{A}, \\ &V_{\text{GE}} = 15\text{V}, \, T_{\text{j}} = 175^{\circ}\text{C} \\ &\text{Inductive load} \end{split}$$
0.01 0 10 20 30 50 Gate Resistance : $R_G[\Omega]$

Fig.15 Typical Capacitance vs. Collector to Emitter Voltage 100000 C_{ies} 10000 Capacitance [pF] 1000 Coes 100 C_{res} 10 f = 1MHz $V_{GE} = 0V$ T; = 25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage: V_{CE} [V]



• Electrical Characteristic Curves

Fig.17 Typical IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

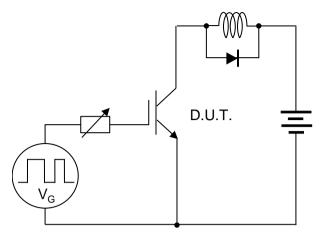


Fig.18 Inductive Load Circuit

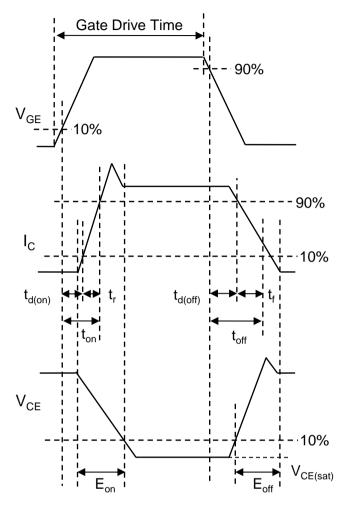


Fig.19 Inductive Load Waveform

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